

isc N-Channel MOSFET Transistor

BUK455-60A/B

DESCRIPTION

- High speed switching
- Easy driver for cost effective application

APPLICATIONS

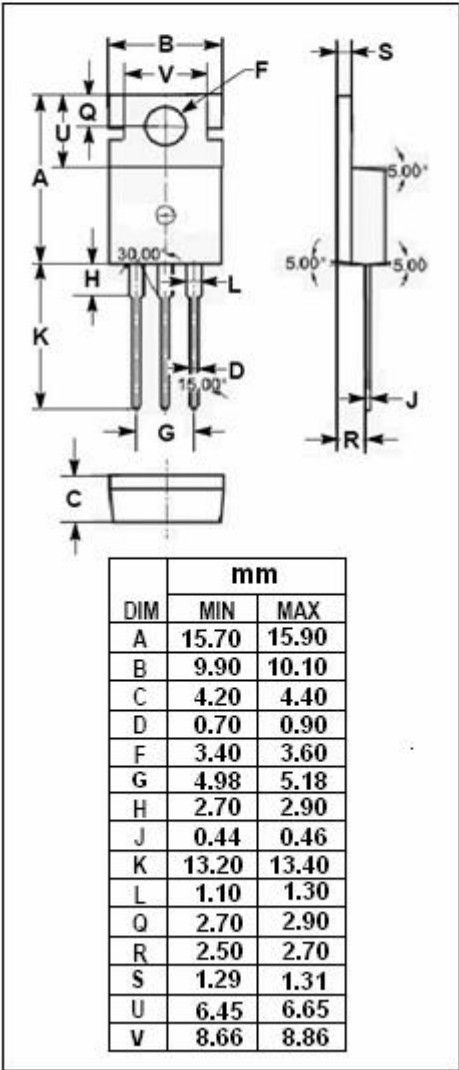
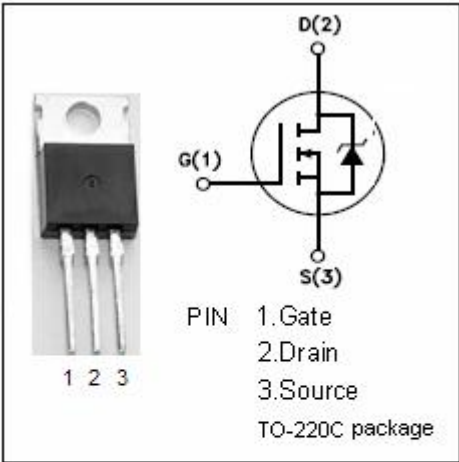
- use in Switched Mode Power Supplies (SMPS), motor control,welding, And in general purpose switching resistance application

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	ARAMETER		VALUE	UNIT
V _{DSS}	Drain-Source Voltage (V _{GS} =0)		60	V
V _{GS}	Gate-Source Voltage		±30	V
I _D	Drain Current-continuou s@ TC=37℃	BUK455-60A	41	A
		BUK455-60B	38	
P _{tot}	Total Dissipation@TC=25℃		125	W
T _j	Max. Operating Junction Temperature		175	℃
T _{stg}	Storage Temperature Range		175	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance,Junction to Case	1.2	°C/W
R _{th j-a}	Thermal Resistance,Junction to Ambient	60	°C/W



isc N-Channel Mosfet Transistor**BUK455-60A/B****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 0.25mA	60		V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = 1mA	2.1	4	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = 10V; I _D = 20A		0.038	Ω
		BUK455-60A BUK455-60B		0.045	
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±30V; V _{DS} = 0		±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 60V; V _{GS} = 0		10	uA
V _{SD}	Diode Forward Voltage	I _F = 41A; V _{GS} = 0		2.0	V